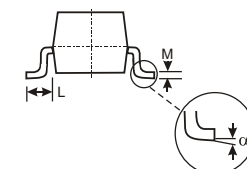
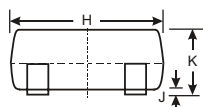
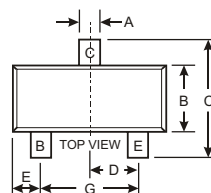


Features

- Excellent h_{FE} Linearity.
- Low noise.
- PNP complement:A733.
- Marking Code:CR



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

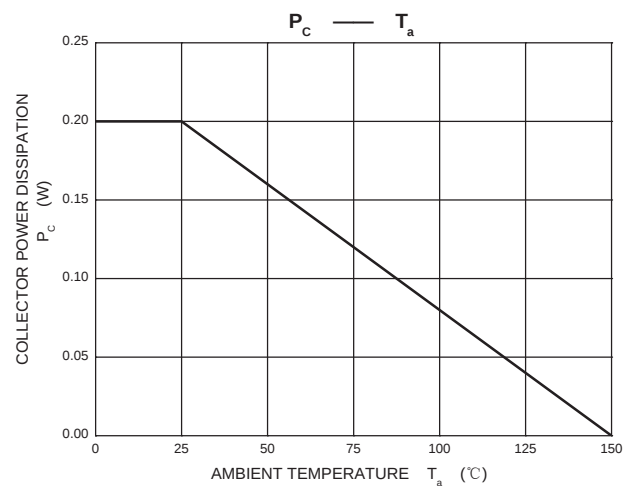
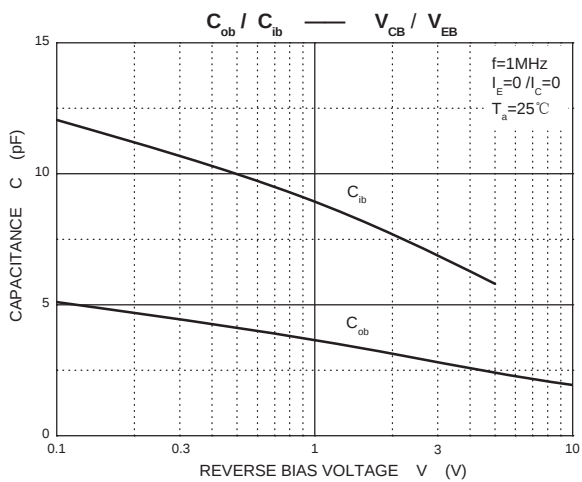
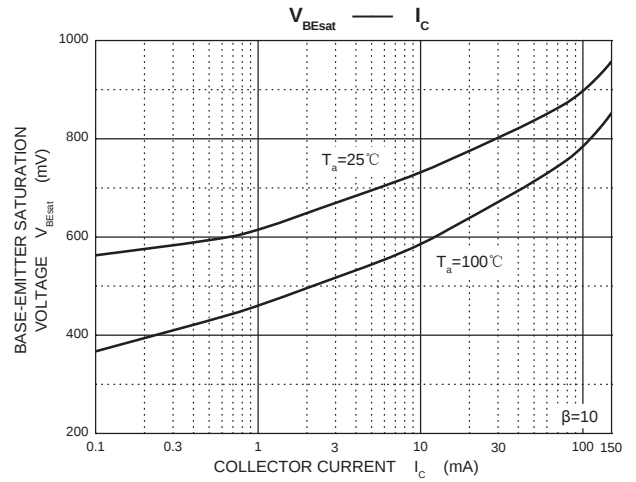
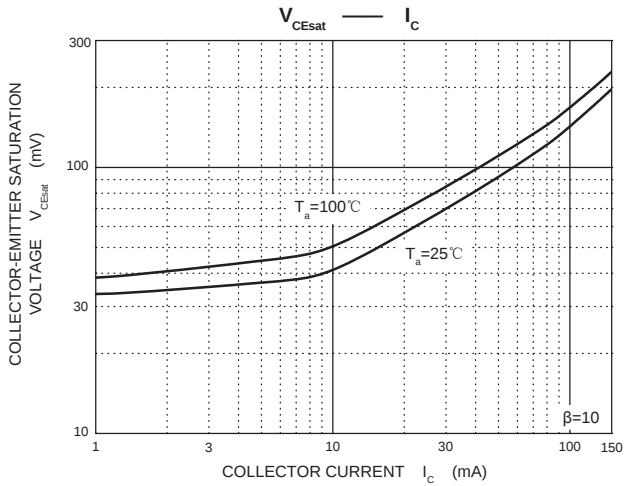
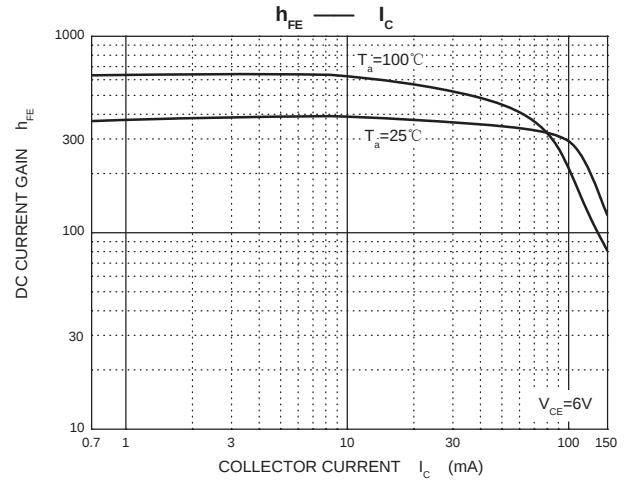
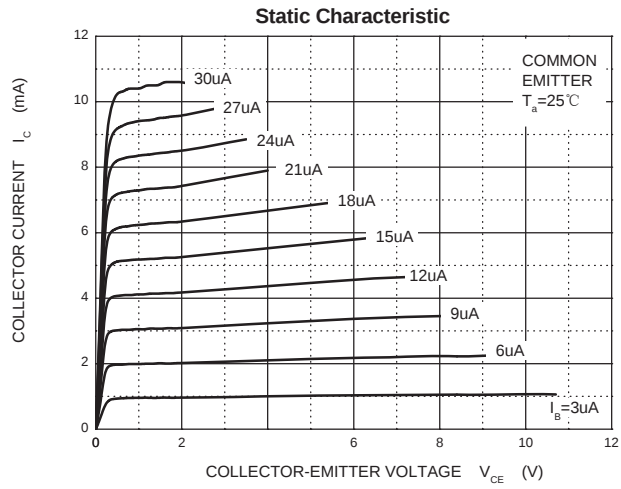
Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	150	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	$I_C=1\text{mA}$, $I_B=0$	50			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	$I_E=0.1\text{mA}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CER}	$V_{CE}=55\text{V}$, $R=10\text{M}\Omega$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6\text{V}$, $I_C=1\text{mA}$	200		400	
	$h_{FE(2)}$	$V_{CE}=6\text{V}$, $I_C=0.1\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=6\text{V}$, $I_C=10\text{mA}$, $f=30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$			3.0	pF
Noise figure	NF	$V_{CE}=6\text{V}$, $I_C=0.1\text{mA}$ $R_g=10\text{k}\Omega$, $f=1\text{kHz}$		4	10	dB

TYPICAL TRANSIENT CHARACTERISTICS



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